

UNITED STATES PATENT AND TRADEMARK OFFICE



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	F.	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09/653,411		08/31/2000	Whonchee Lee	M4065.0361/P361	5349	
24998	7590	06/18/2004		EXAM	INER	
		IRO MORIN & OS	NGUYEN, JOSEPH H			
2101 L STR WASHING		20037-1526		ART UNIT	ART UNIT PAPER NUMBER	
				2815		

DATE MAILED: 06/18/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

				r
		Application No.	Applicant(s)	
		09/653,411	LEE ET AL.	
Office Action Sum	mary	Examin r	Art Unit	
		Joseph Nguyen	2815	
The MAILING DATE of this Period for Reply	s communication app	ears on the cover sheet with the o	correspond nce address	
 If NO period for reply is specified above, the Failure to reply within the set or extended p 	COMMUNICATION. the provisions of 37 CFR 1.13 e of this communication. s than thirty (30) days, a reply e maximum statutory period w eriod for reply will, by statute, hree months after the mailing		mely filed ys will be considered timely. In the mailing date of this communication. ED (35 U.S.C. § 133).	·
1) Responsive to communica				
2a) This action is FINAL .	<i>'</i> —	action is non-final.		
· · · · · · · · · · · · · · · · · · ·		ice except for formal matters, prox parte Quayle, 1935 C.D. 11, 4		
Disposition of Claims				
4)	is/are withdrav wed. cted. cted to.	vn from consideration.		
Application Papers				
9)☐ The specification is objecte	ed to by the Examine	r.		
10)⊠ The drawing(s) filed on <u>31</u>	August 2000 is/are:	a)⊠ accepted or b)□ objected	to by the Examiner.	
		drawing(s) be held in abeyance. Se		
Replacement drawing sheet(on is required if the drawing(s) is ob aminer. Note the attached Office		
Priority under 35 U.S.C. § 119				
2. Certified copies of the3. Copies of the certified application from the	None of: he priority documents he priority documents ed copies of the prior International Bureau	s have been received. s have been received in Applicat ity documents have been receiv	tion No red in this National Stage	
Attachment(s)		_		
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawin 		4)		
 Notice of Draftsperson's Patent Drawin Information Disclosure Statement(s) (F Paper No(s)/Mail Date <u>02/06/2004</u>. 			Patent Application (PTO-152)	

Art Unit: 2815

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 39- 47, 49-50 are rejected under 35 U.S.C. 102(b) as being anticipated by Lee et al (2001/0025976 A1).

Regarding claim 39, Lee et al discloses on figure 5 a semiconductor device comprising a substrate 31 and at least one electron mechanically polished metal layer 53 formed over said substrate 31, said electro mechanically polished metal layer's surface has been electro-mechanically polished against a second surface while submersed in an electric bath.

It should be noted that the term "electro-mechanical polished against a second surface while submersed in an electric bath" merely recites product by process and does not structurally distinguish the metal layer from the structure taught by Lee et al.

Regarding claim 40, Lee et al disclose on figure 5 the metal layer 53 comprises at least one metal selected from the group consisting of noble metals, noble metal alloys, refractory metals and refractory metal alloys.

Regarding claim 41, Lee et al disclose on figure 5 the device comprises a capacitor with at least one electro mechanical polished metal layer 53.

Regarding claim 42, Lee et al disclose on figure 5 the electro-mechanical polished metal layer 53 is bottom electrode of said capacitor.

Regarding claim 43, Lee et al disclose on figure 5 a semiconductor device comprising a bottom electrode 53 formed over a substrate 31; an insulating layer 55 formed over the bottom electrode; and a top electrode 57 formed over the insulating layer 55, wherein at least one electrode surface comprises an electro mechanically polished surface that has been electro-mechanically polished against a second surface while submersed in an electric bath.

It should be noted that the term "electro-mechanical polished against a second surface while submersed in an electric bath" merely recites product by process and does not structurally distinguish the metal layer from the structure taught by Lee et al.

Regarding claim 44, Lee et al disclose on figure 5 the capacitor is a MIM capacitor.

Regarding claim 45, Lee et al disclose on figure 5 at least one electrode 53 comprises a metal selected from the group consisting of noble metals, noble metal alloys, refractory metals and refractory metal alloys.

Regarding claim 46, Lee et al disclose on figure 5 at least one electrode surface is a surface of the bottom electrode 53.

Regarding claim 47, Lee et al disclose on figure 5 the bottom electrode 53 comprises a platinum electrode.

Art Unit: 2815

Regarding claim 49, Lee et al discloses on figure 5 a semiconductor device comprising a substrate 31; and at least one electro-mechanically polished metal layer 53 consisting of a noble metal formed.

Regarding claim 50, Lee et al discloses on figure 5 a semiconductor device comprising a bottom electrode 53 formed over a substrate 31; an insulating layer 55 formed over said bottom electrode; and a top electrode 57 formed over said insulating layer, wherein at least one electrode surface comprises an electro mechanically polished noble metal surface.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 48 and 51 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lee et al in view of Sandhu et al.

Regarding claims 48 and 51, Lee et al disclose substantially all the structure set forth in the claimed invention except a memory device electrically coupled to a processor. However, Sandhu et al disclose on figure 20 a memory device 1100 electrically coupled to a processor. In view of such teaching, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lee et al

Application/Control Number: 09/653,411 Page 5

Art Unit: 2815

by having a memory device electrically coupled to a processor for the purpose of improving the performance of the integrated circuits.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Joseph Nguyen whose telephone number is (571) 272-1734. The examiner can normally be reached on Monday-Friday, 7:30 am- 4:30 pm

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306 for regular communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

JN June 17, 2004

> JEROME JACKSON PRIMARY EXAMINER